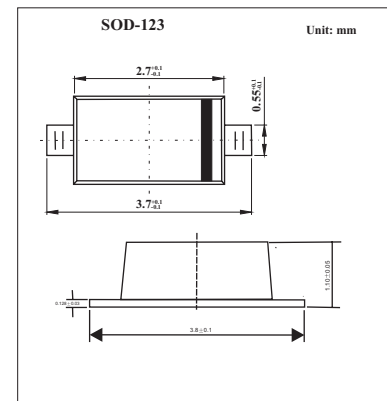


Schottky Barrier Diode RB160M-30

■ Features

- Small power mold type.
- Low I_R
- High reliability



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

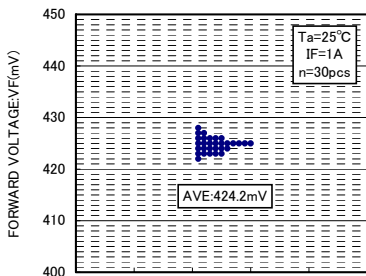
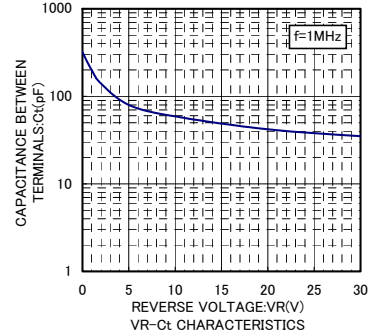
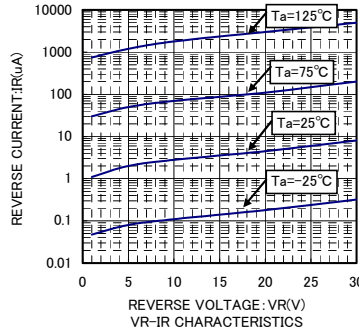
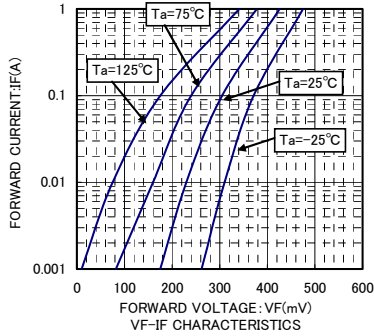
Parameter	Symbol	Rating	Unit
Reverse voltage	V_{RM}	30	V
reverse voltage	V_R	30	V
Forward current surge peak	I_o	1	A
Average rectified forward current	I_{FSM}	30	A
operating junction temperature	T_j	125	$^\circ\text{C}$
storage temperature	T_{stg}	-40 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

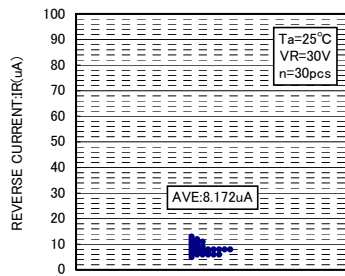
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Forward voltage	V_{F1}	$I_F=0.5\text{A}$		0.39	0.46	V
	V_{F2}	$I_F=1.0\text{A}$		0.43	0.48	V
Reverse current	I_{R1}	$V_R=15\text{V}$		3.0	20	μA
	I_{R2}	$V_R=30\text{V}$		9.0	50	μA

RB160M-30

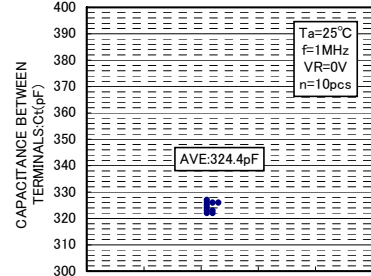
●Electrical characteristic curves (Ta=25°C)



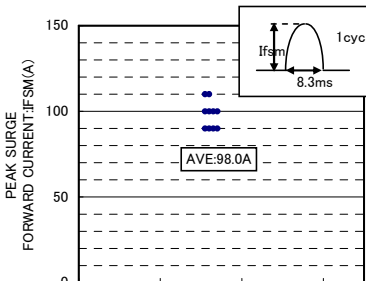
VF DISPERSION MAP



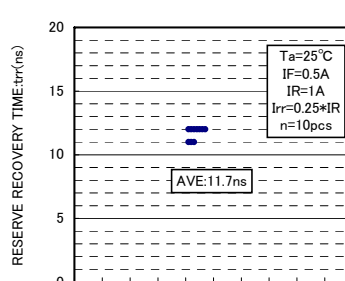
IR DISPERSION MAP



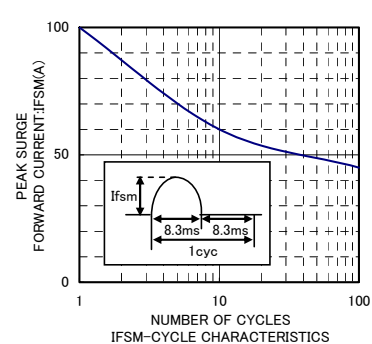
Ct DISPERSION MAP



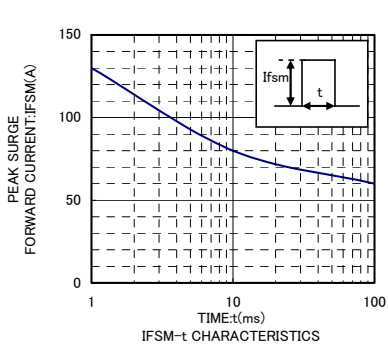
IFSM DISERSION MAP



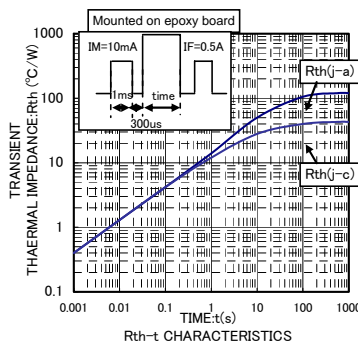
trr DISPERSION MAP



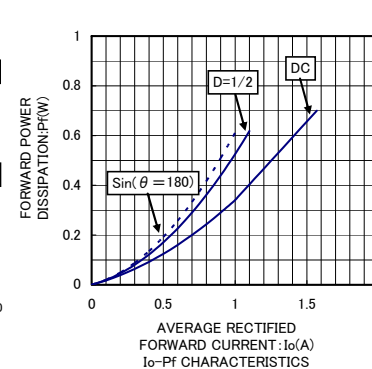
IFSM-CYCLE CHARACTERISTICS



IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



Io-PF CHARACTERISTICS